



Ruttonsha International Rectifier Ltd.

SILICON CONTROLLED RECTIFIERS

High Power Thyristor Hockey Puk Version U-PUK Series 3500PU

Type : 3500 PU...

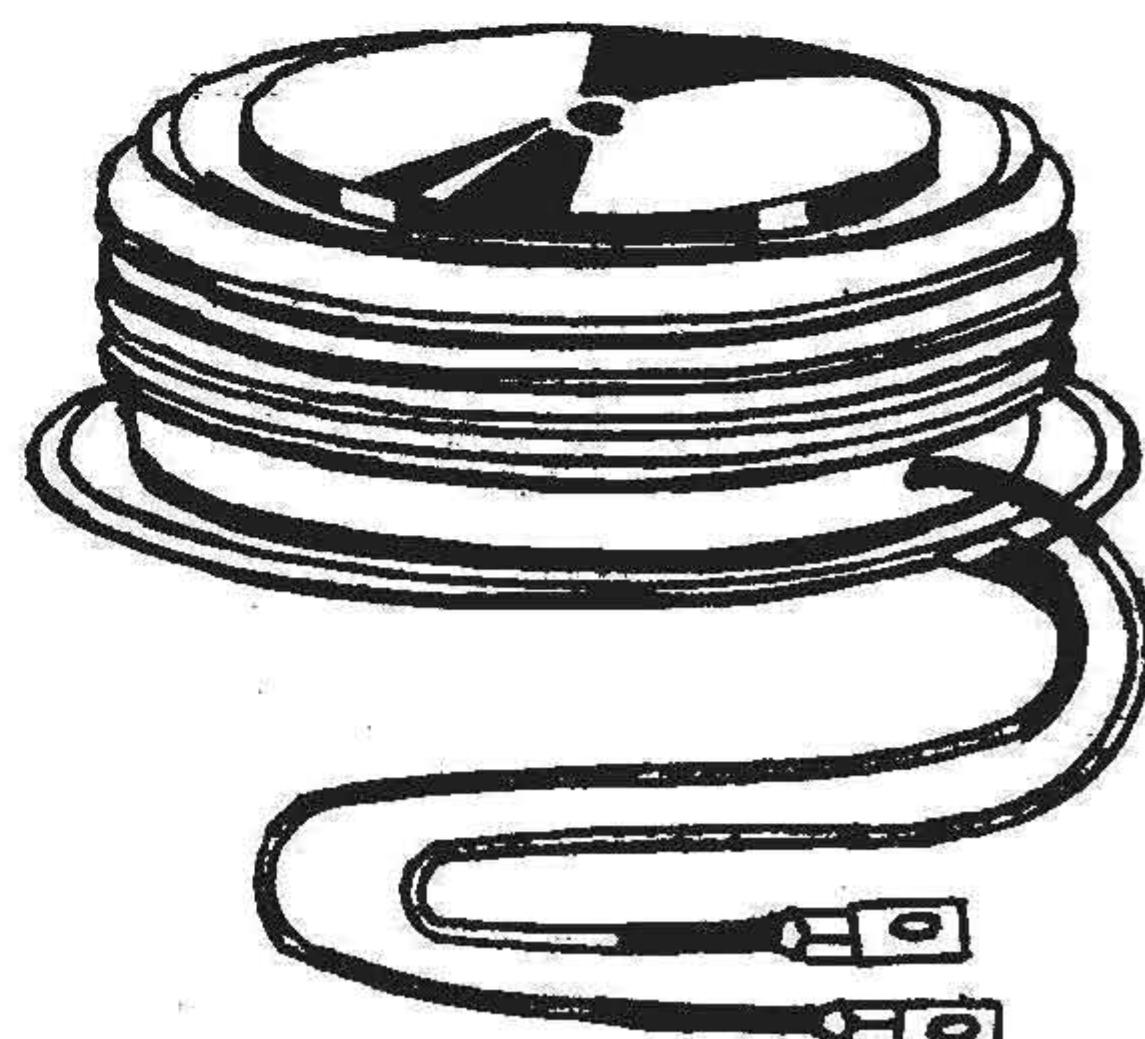
FEATURES

- ❖ Center amplifying gate.
- ❖ Metal case with ceramic insulator
- ❖ High profile hockey - puk.

TYPICAL APPLICATIONS

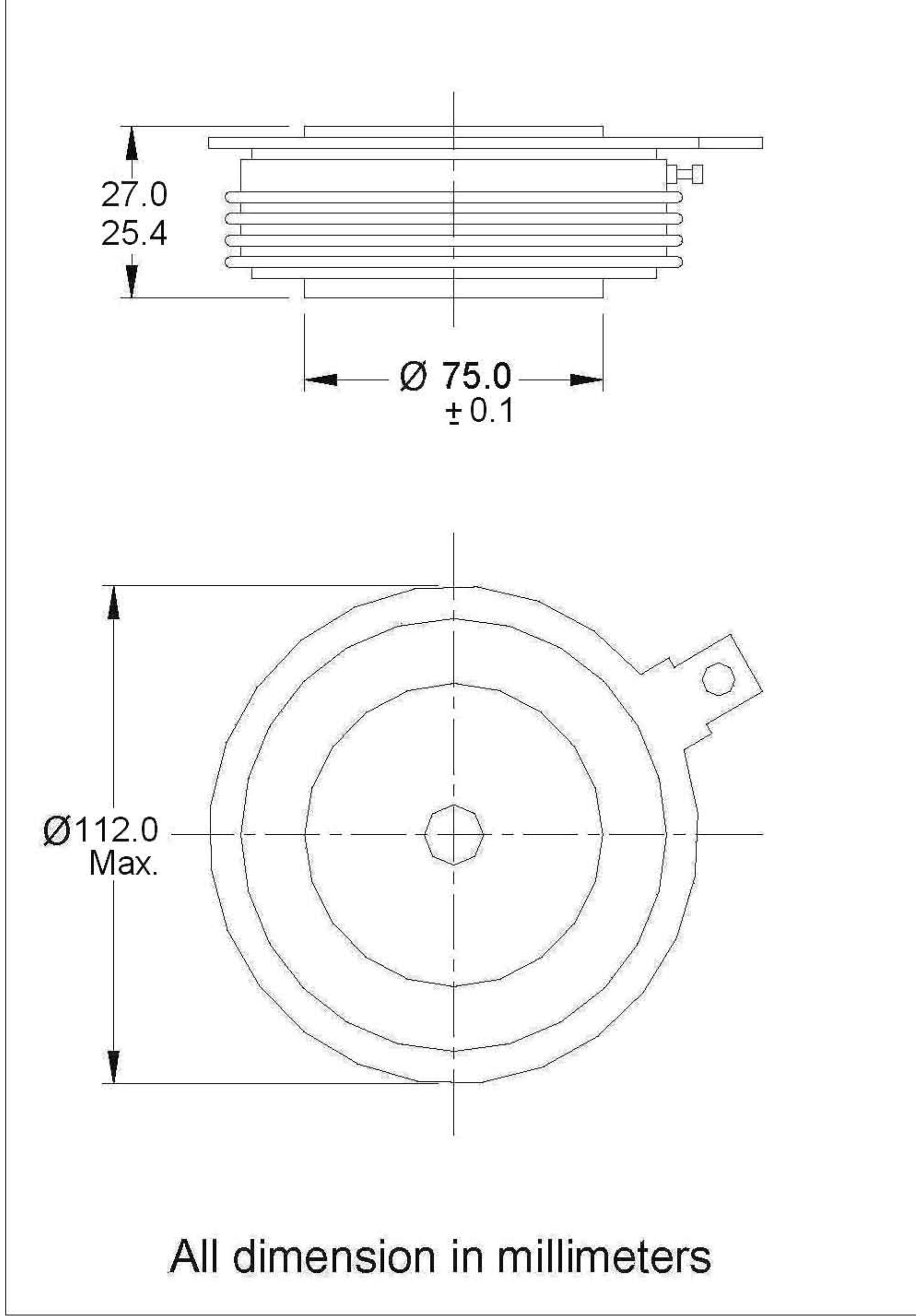
- ❖ DC motor control (e.g. for machine tools).
- ❖ Controlled rectifiers (e.g. for battery charging, Uninterrupted Power Supply).
- ❖ AC controllers (e.g. for temperature control, lights control).

3500 PU... (U - PUK)



Major Ratings and Characteristics

Parameter	3500PU	Units
$I_{T(AV)}$ @ T_{hs}	3476	A
$I_{T(RMS)}$ @ T_{hs}	6787	A
I_{TSM} @ 50 Hz	52	KA
I^2t @ 50 Hz	13520	KA ² s
V_{DRM}/V_{RRM}	2200 - 3200	V
t_q typical	550	μ s
T_J	-40 to +125	°C



All dimension in millimeters

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ELECTRICAL SPECIFICATIONS

Type : 3500 PU Series

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_{J\max}$ mA
3500PU	220	2200	2300	250
	240	2400	2500	
	260	2600	2700	
	280	2800	2900	
	300	3000	3100	
	320	3200	3300	

On - state Conduction

Parameter	3500PU	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	3476	A	180° conduction, half sine wave double side cooled
	55	°C	
$I_{T(RMS)}$ Max RMS on-state current	6787	A	DC @ 55 °C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	52	KA	t = 10 ms Sinusoidal half wave, Initial $T_J = T_{J\max}$.
I^2t Maximum I^2t for fusing	13520	KA ² s	t = 10 ms
$V_{T(TO)}$ Threshold voltage	0.97	V	
r_t On-state slope resistance	0.18	mΩ	
V_{TM} Max. on state voltage	1.87	V	$I_{PK} = 5000 \text{ A}, T_J = T_{J\max}, t_p = 10 \text{ ms sine pulse}$
I_H Maximum holding current	1000	mA	$T_J = 25^\circ\text{C}$, anode supply 12 V resistive load

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Switching

Parameter	3500PU	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	100	A/μs	Gate drive 20V, 20Ω , $t_r \leq 1\mu s$ $T_J = T_{J\max}$ max. anode voltage ≤ 80% V_{DRM}
t_q Typical turn-off time	550	μs	$I_{TM} = 4000 A$, $T_J = T_{J\max}$ max. di/dt = 10A/μs , $V_R = 50V$ $dv/dt = 20 V/\mu s$, 0.8 V_{DRM} Reapplied , $t_p = 2ms$

Blocking

Parameter	3500PU	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_{J\max}$ linear to 80% rated V_{DRM}
I_{RRM} Max. peak reverse and off-state leakage current	250	mA	$T_J = T_{J\max}$ rated V_{DRM} / V_{RRM} applied

Triggering

Parameter	3500PU	Units	Conditions
P_{GM} Maximum peak gate power	50	W	$T_J = T_{J\max}$, $t_p \leq 5 ms$
$P_{G(AV)}$ Maximum average gate power	5		$T_J = T_{J\max}$, $f = 50Hz$, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_{J\max}$, $t_p \leq 5 ms$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_{J\max}$, $t_p \leq 5 ms$
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger	300	mA	$T_J = 25^\circ C$ Max.required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode-to-cathode applied
V_{GT} DC gate voltage required to trigger	3.0	V	$T_J = 25^\circ C$
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_{J\max}$. Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

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Thermal and Mechanical Specifications

Parameter	3500PU	Units	Conditions
T_J	Max.operating temperature range	-40 TO +125	$^{\circ}\text{C}$
T_{stg}	Max.storage temperature range	-40 TO +150	
$R_{\text{thJ-hs}}$	Max. thermal resistance, junction to heatsink	0.008	K/W DC operation double side cooled
F	Mounting force, $\pm 10\%$,	63 TO 77	KN
wt.	Approximate weight	1400	g
Case style		U - PUK	See Outline Table

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Curves

Figure 1 - On-state characteristics of Limit device

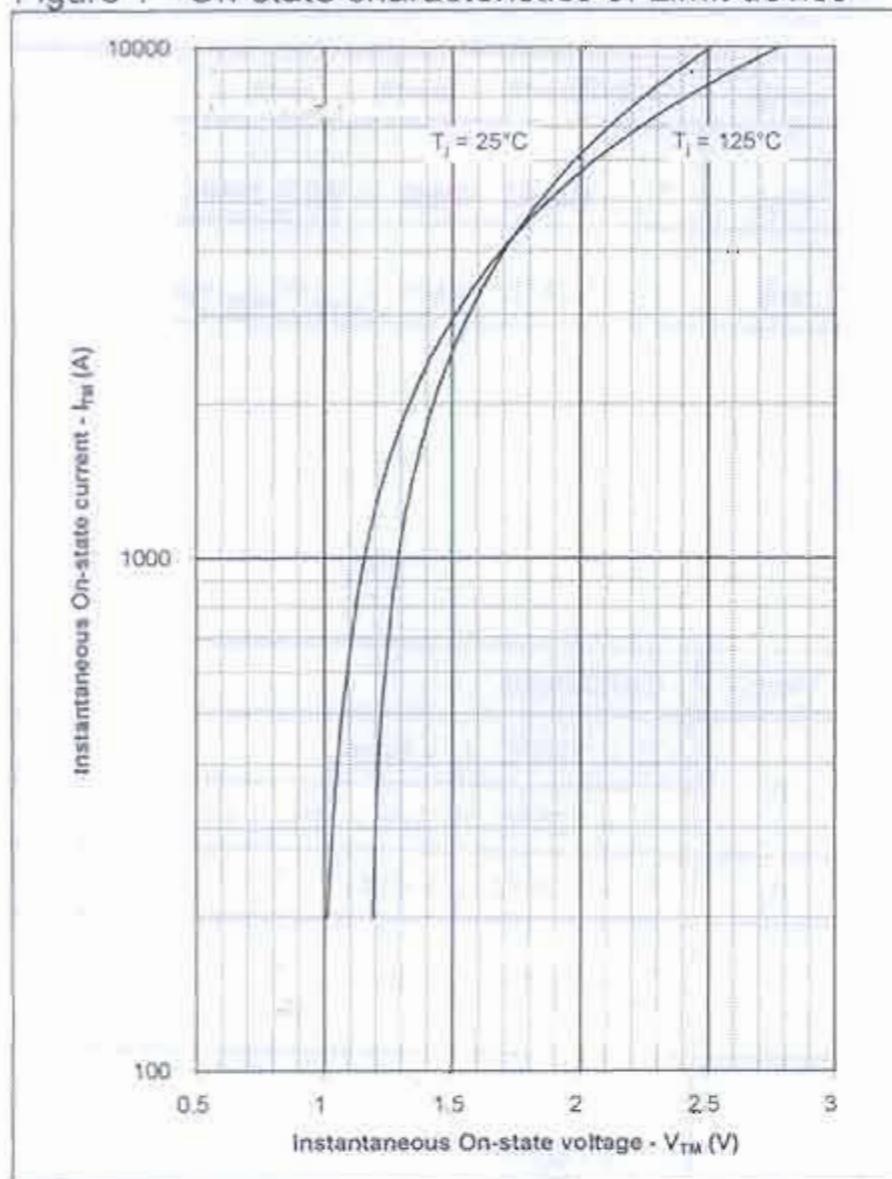


Figure 2 - Transient thermal impedance

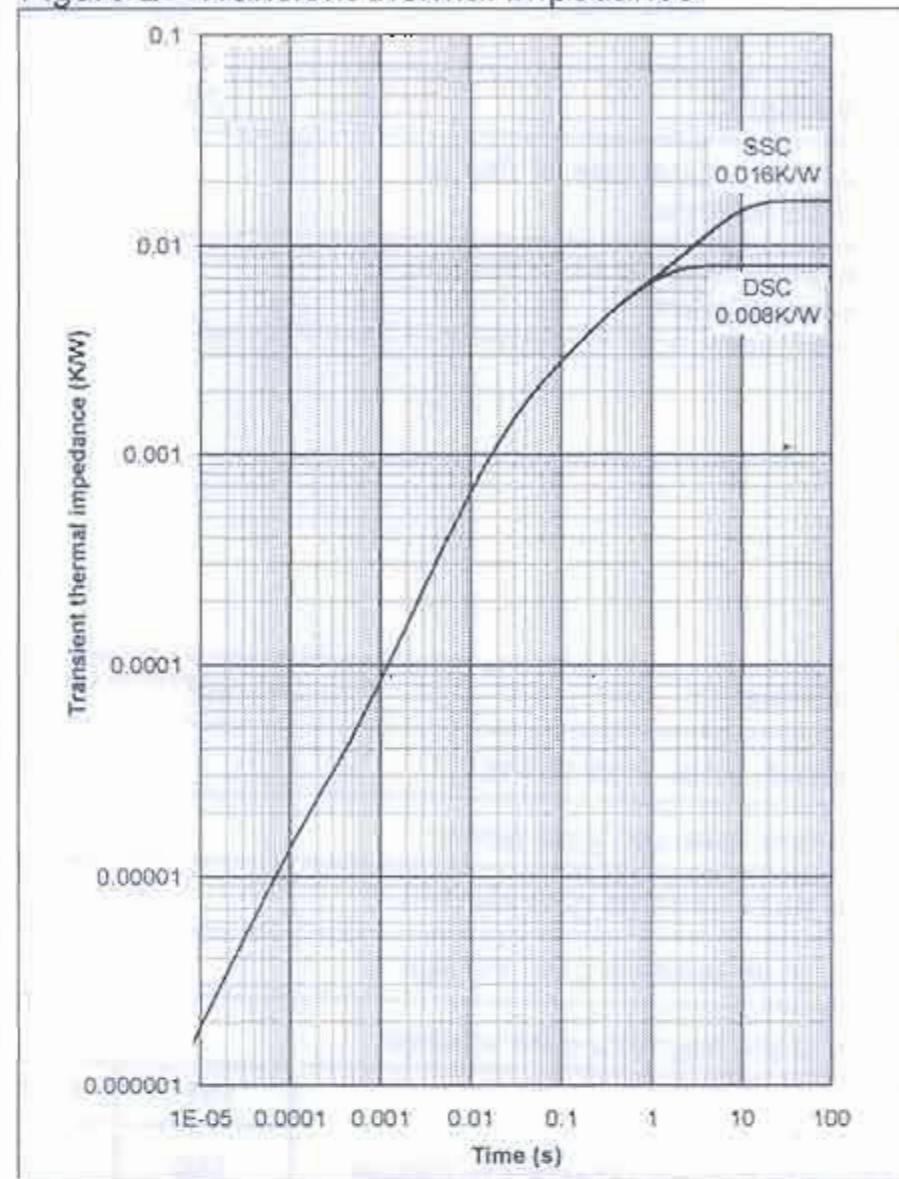


Figure 3 - Gate characteristics - Trigger limits

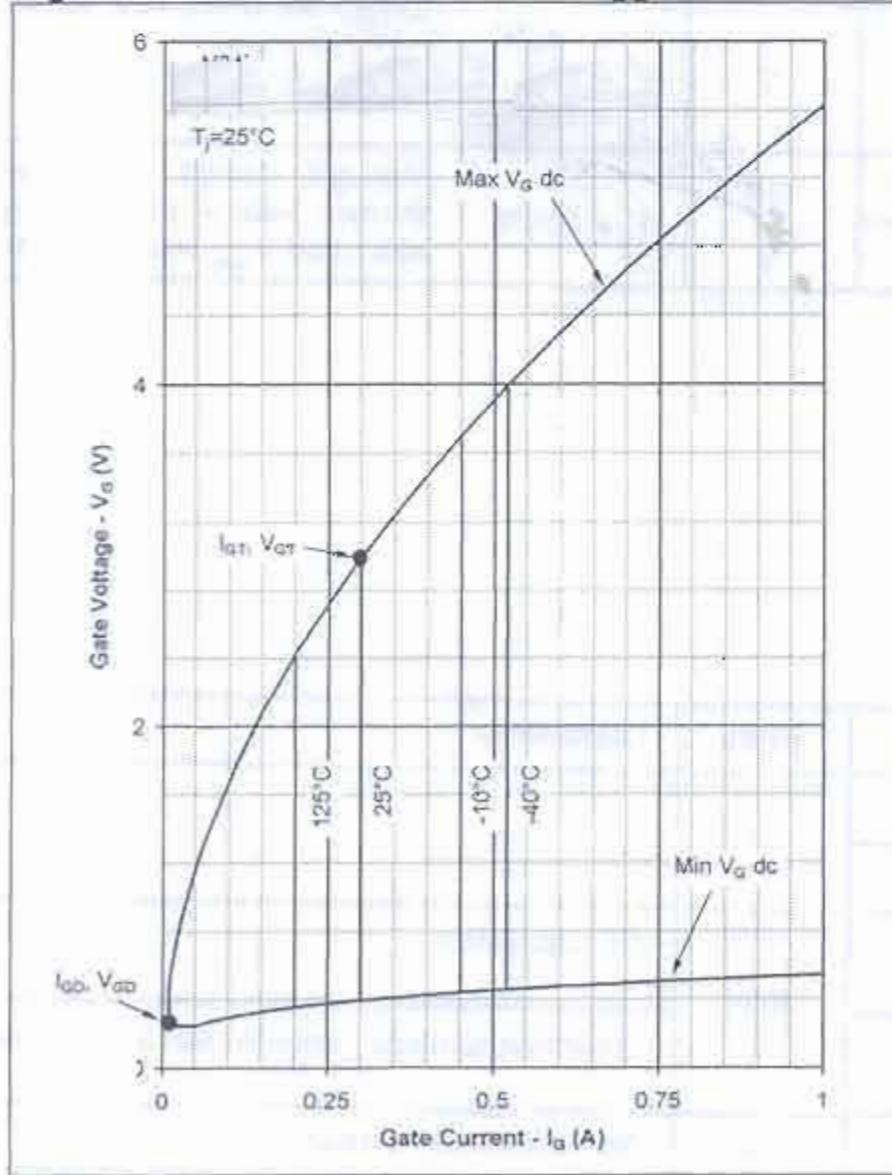
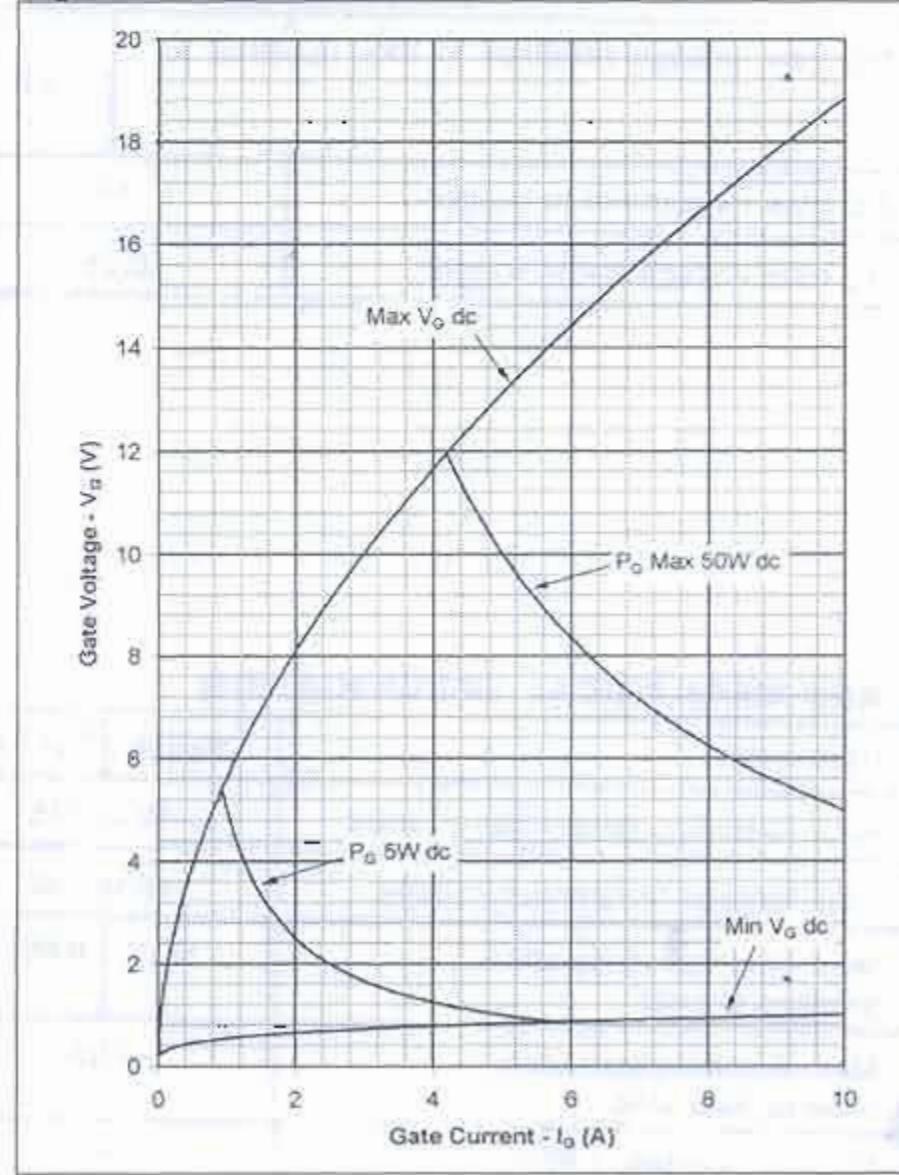


Figure 4 - Gate characteristics - Power curves



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Figure 9 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

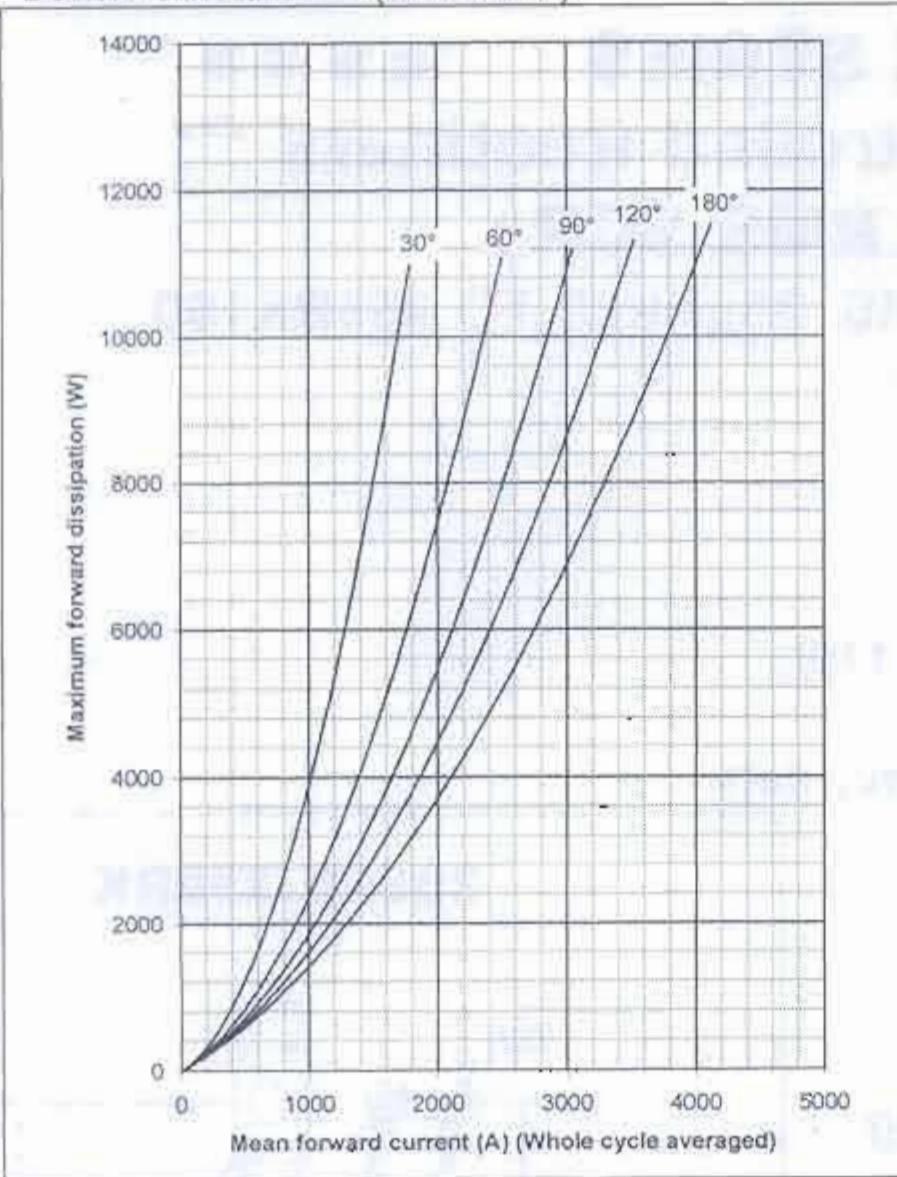


Figure 10 – On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

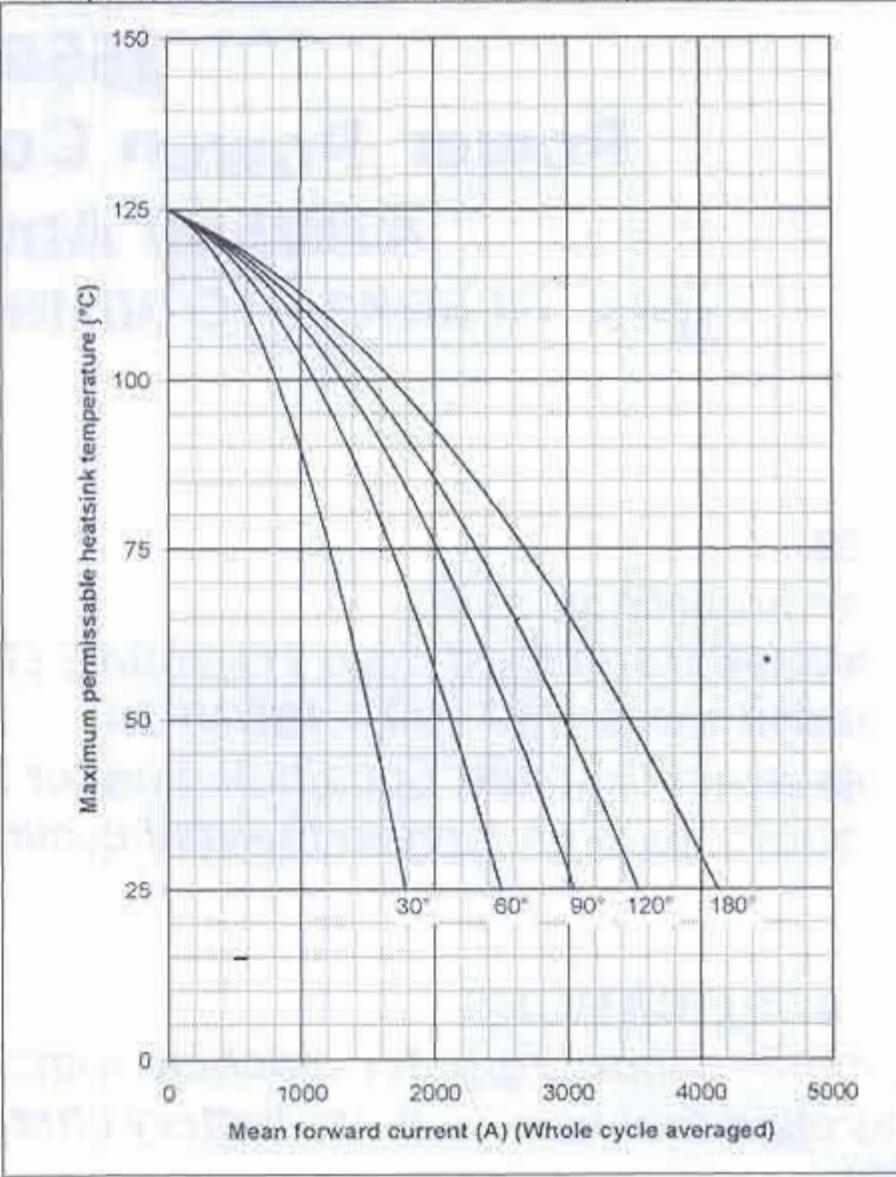


Figure 11 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

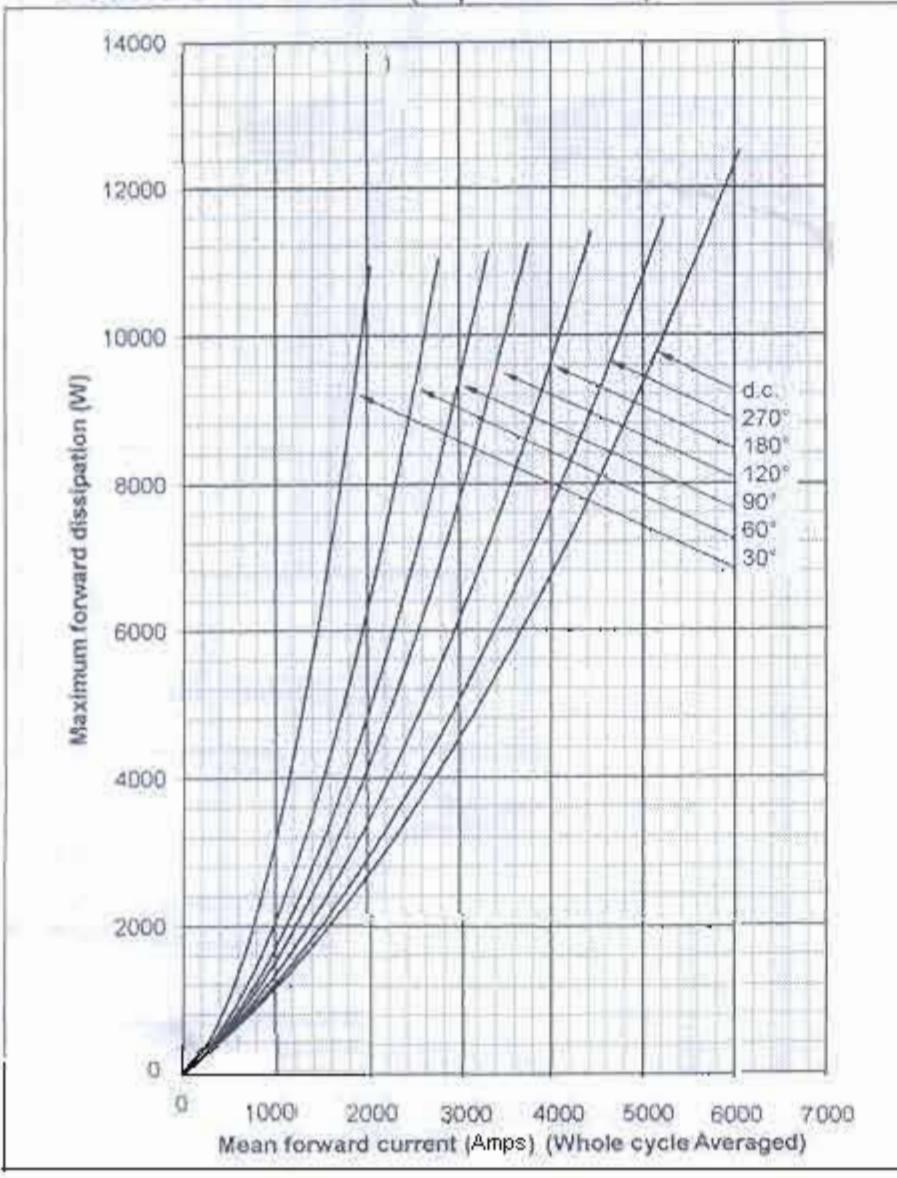
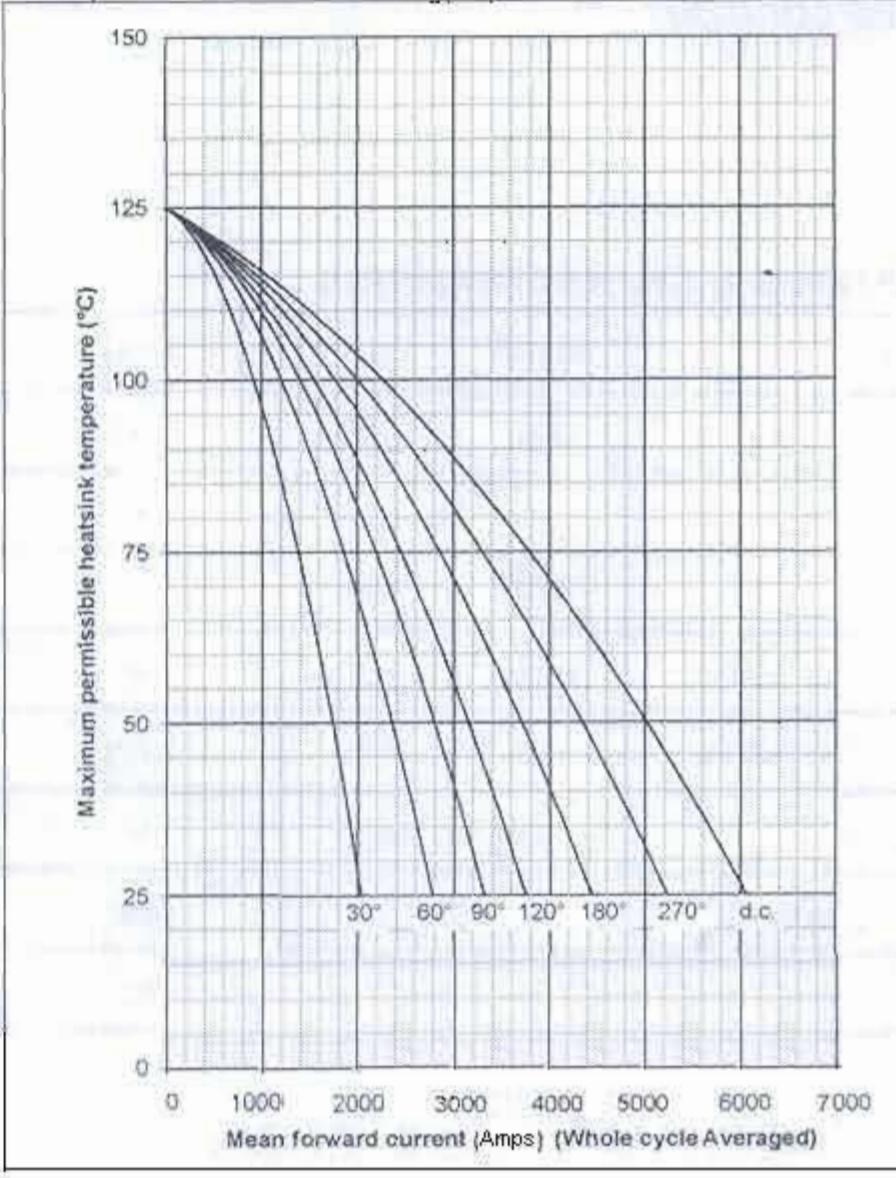


Figure 12 – On-state current vs. Heatsink temperature – Double Side Cooled (Square wave)



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Figure 17 - Maximum surge and I^2t Ratings

